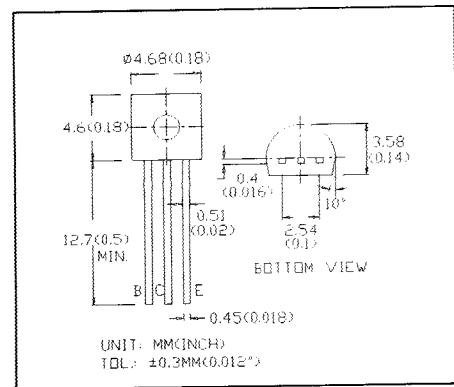


DESCRIPTION

2N5367(R) is PNP silicon planar transistor use in general purpose consumer and industrial amplifier and switching applications.

TO-92B



ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage

V_{CEO} 32V

Collector-Base Voltage

V_{CBO} 40V

Emitter-Base Voltage

V_{EBO} 4V

Collector Current

I_C 300mA

Continuous Power Dissipation

P_d 360mW

Operating & Storage Junction Temperature

T_j, T_{stg} -55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS

($T_a = 25^\circ C$)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS
Collector-Emitter Breakdown Voltage	V_{CEO}^*	32		V	$I_C = 10mA$ $I_B = 0$
Collector Cutoff Current	I_{CBO}		100	nA	$V_{CB} = 40V$ $I_E = 0$
Collector Cutoff Current	I_{CES}		100	nA	$V_{CB} = 40V$ $V_{EB} = 0$
Emitter Cutoff Current	I_{EBO}		10	μA	$V_{EB} = 4V$ $I_C = 0$
D.C. Current Gain	H_{FE}^*	170			$I_C = 2mA$ $V_{CE} = 10V$
		170	500		$I_C = 50mA$ $V_{CE} = 1V$
		50			$I_C = 300mA$ $V_{CE} = 5V$
Base-Emitter Voltage	V_{BE}		0.8	V	$I_C = 2mA$ $V_{CE} = 10V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}^*$		0.25	V	$I_C = 50mA$ $I_B = 2.5mA$
			1	V	$I_C = 300mA$ $I_B = 30mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}^*$		1.1	V	$I_C = 50mA$ $I_B = 2.5mA$
			2	V	$I_C = 300mA$ $I_B = 30mA$
Small Signal Current Gain	h_{fe}	200			$I_C = 2mA$ $V_{CE} = 10V$
					$f = 1kHz$
Output Capacitance	C_{ob}		8	pF	$V_{CB} = 10V$ $f = 1MHz$
Input Capacitance	C_{ib}		35	pF	$V_{EB} = 0.5V$ $f = 1MHz$
Current Gain-bandwidth Product	f_T	200	TYP	pF	$I_C = 2mA$ $V_{CE} = 10V$

* Pulse test, pulse width < 300 μ S, duty cycle < 2%.

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